

FEATURES

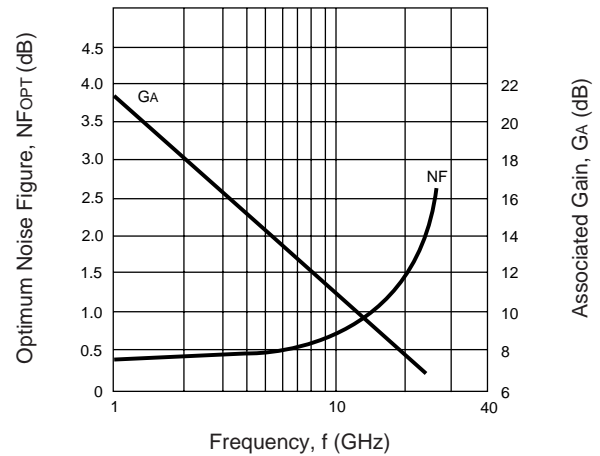
- **VERY LOW NOISE FIGURE:**
0.75 dB typical at 12 GHz
- **HIGH ASSOCIATED GAIN:**
10.5 dB Typical at 12 GHz
- **GATE LENGTH:** 0.3 μm
- **GATE WIDTH:** 280 μm

DESCRIPTION

The NE23300 is a Hetero-Junction FET chip that utilizes the junction between Si-doped AlGaAs and undoped InGaAs to create a two-dimensional electron gas layer with very high electron mobility. Its excellent low noise figure and high associated gain make it suitable for space applications.

NEC's stringent quality assurance and test procedures assure the highest reliability and performance.

NOISE FIGURE & ASSOCIATED GAIN vs. FREQUENCY
 $V_{DS} = 2\text{ V}, I_{DS} = 10\text{ mA}$



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PART NUMBER PACKAGE OUTLINE			NE23300 00 (Chip)		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
NF_{OPT}^1	Noise Figure, $V_{DS} = 2\text{ V}, I_D = 10\text{ mA}$, f = 4 GHz f = 12 GHz	dB dB		0.35 0.75	1.0
GA^1	Associated Gain, $V_{DS} = 2\text{ V}, I_D = 10\text{ mA}$, f = 4 GHz f = 12 GHz	dB dB	10.0	15.0 10.5	
P_{1dB}	Output Power at 1 dB Gain Compression Point, f = 12 GHz $V_{DS} = 2\text{ V}, I_{DS} = 10\text{ mA}$ $V_{DS} = 2\text{ V}, I_{DS} = 20\text{ mA}$	dBm dBm		11.2 12.0	
G_{1dB}	Gain at P_{1dB} , f = 12 GHz $V_{DS} = 2\text{ V}, I_{DS} = 10\text{ mA}$ $V_{DS} = 2\text{ V}, I_{DS} = 20\text{ mA}$	dB dB		11.8 12.8	
I_{DSS}	Saturated Drain Current, $V_{DS} = 2\text{ V}, V_{GS} = 0\text{ V}$	mA	15	40	80
V_P	Pinch-off Voltage, $V_{DS} = 2\text{ V}, I_D = 100\text{ }\mu\text{A}$	V	-2.0	-0.8	-0.2
g_m	Transconductance, $V_{DS} = 2\text{ V}, I_D = 10\text{ mA}$	mS	45	70	
I_{GSO}	Gate to Source Leakage Current, $V_{GS} = -5\text{ V}$	μA		0.5	10
$R_{TH(CH-C)}^2$	Thermal Resistance (Channel to Case)	$^\circ\text{C/W}$			260

Notes:

1. RF performance is determined by packaging and testing 10 samples per wafer. Wafer rejection criteria for standard devices is 2 rejects for 10 samples.
2. Chip mounted on infinite heat sink.

ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{DS}	Drain to Source Voltage	V	4.0
V _{GS}	Gate to Source Voltage	V	-3.0
I _{DS}	Drain Current	mA	I _{DSS}
T _{CH}	Channel Temperature	°C	175
T _{STG}	Storage Temperature	°C	-65 to +175
P _T	Total Power Dissipation	mW	200

Note:

1. Operation in excess of any one of these parameters may result in permanent damage.

TYPICAL NOISE PARAMETERS¹ (T_A = 25°C)

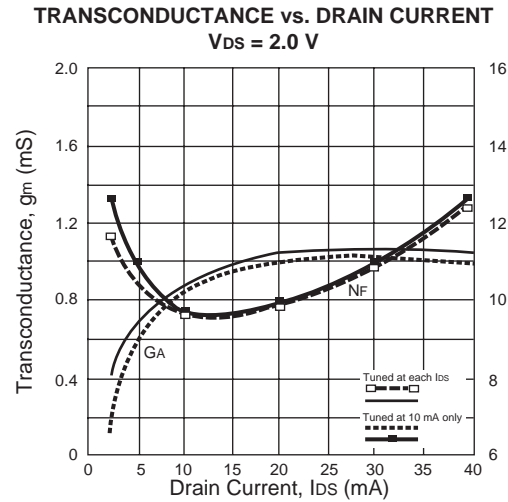
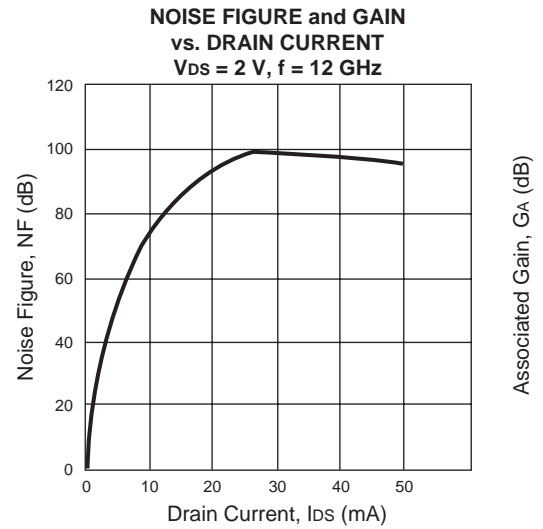
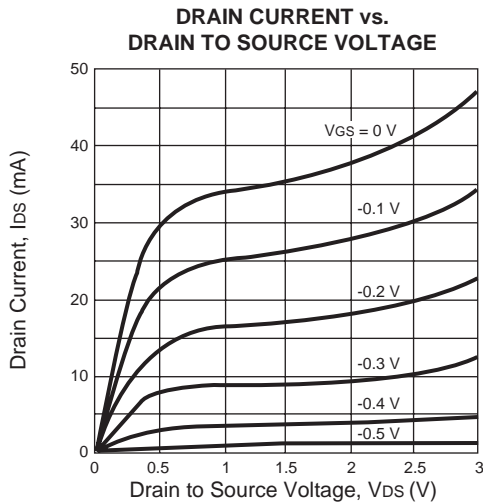
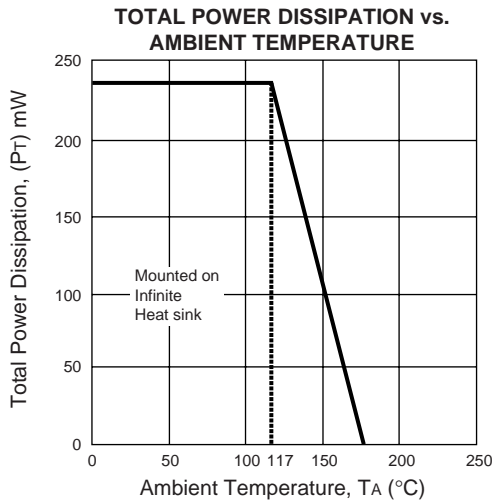
V_{DS} = 2 V, I_{DS} = 10 mA

FREQ. (GHz)	NF _{OPT} (dB)	G _A (dB)	Γ _{OPT}		R _n /50
			MAG	ANG	
1	0.29	21.0	0.82	8	0.39
2	0.31	18.0	0.81	17	0.36
4	0.35	15.0	0.76	41	0.33
6	0.42	13.2	0.71	63	0.30
8	0.52	11.9	0.64	77	0.27
10	0.63	11.0	0.55	95	0.24
12	0.75	10.2	0.48	112	0.22
14	0.9	9.6	0.41	130	0.19
16	1.05	9.0	0.37	144	0.18
18	1.25	8.5	0.35	164	0.15
20	1.5	8.0	0.37	180	0.13
22	1.8	7.6	0.38	-166	0.11
24	2.2	7.3	0.39	-154	0.10
26	2.6	7.0	0.40	-142	0.08

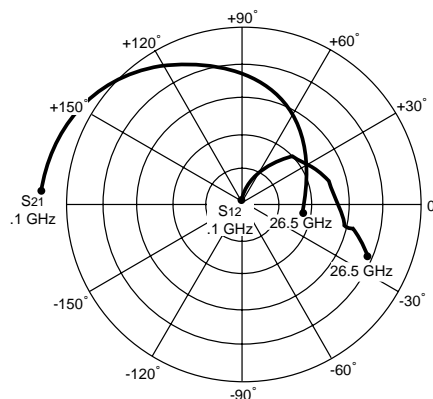
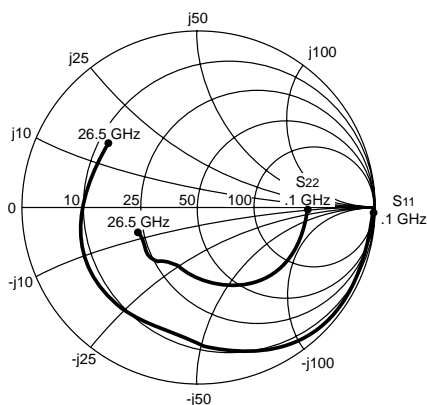
Note:

1. Noise Parameters include Bond Wires:
 - Gate: Total 2 wires, 1 per bond pad 0.0129" (327 μm) long each wire.
 - Drain: Total 2 wires, 1 per bond pad 0.0118" (300 μm) long each wire.
 - Source: Total 4 wires, 2 per side, 0.0071" (180 μm) long each wire.
 - Wire: 0.0007" (17.8 μm) dia. gold.

TYPICAL PERFORMANCE CURVES (T_A = 25°C)



TYPICAL COMMON SOURCE SCATTERING PARAMETERS¹ (T_A = 25°C)



V_{DS} = 2 V, I_{DS} = 10 mA

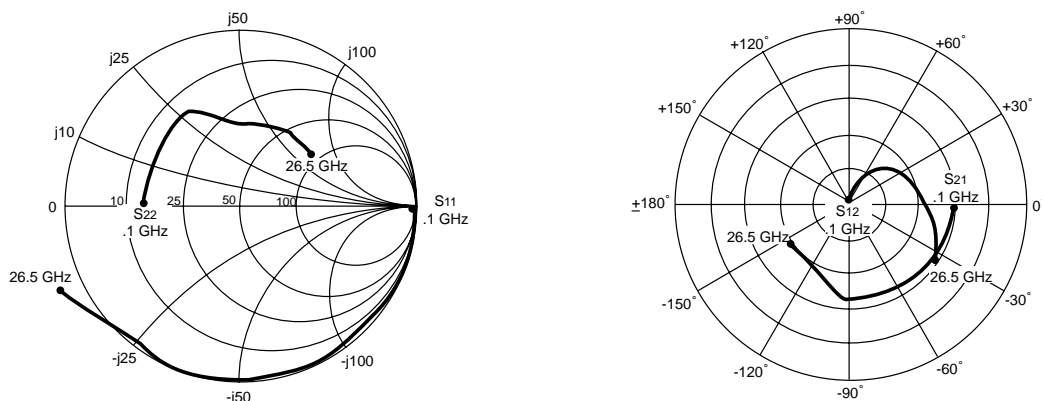
FREQUENCY (GHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	S ₂₁ (dB)	MAG ² (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG			
0.1	.999	-1.8	5.854	178.8	.003	87.5	.631	-1.4	0.05	15.3	32.9
0.2	.999	-3.6	5.850	177.2	.005	86.2	.632	-2.5	0.04	15.4	30.7
0.5	.998	-8.9	5.846	173.5	.011	84.6	.632	-6.1	0.02	15.3	27.3
1.0	.994	-17.7	5.797	167.0	.022	82.0	.628	-12.1	0.00	15.3	24.2
2.0	.974	-34.6	5.614	154.1	.044	71.2	.618	-23.8	0.04	15.0	21.1
3.0	.940	-49.9	5.299	142.1	.063	62.4	.598	-34.9	0.09	14.5	19.2
4.0	.903	-63.2	4.919	131.1	.079	52.5	.578	-43.9	0.17	13.8	17.9
5.0	.861	-75.1	4.512	121.4	.089	46.4	.556	-51.5	0.23	13.1	17.0
6.0	.822	-85.9	4.210	112.5	.099	39.7	.532	-59.1	0.29	12.5	16.3
7.0	.798	-93.2	3.900	105.5	.103	35.2	.528	-60.8	0.35	11.8	15.8
8.0	.750	-102.2	3.642	97.8	.103	27.7	.495	-65.1	0.48	11.2	15.5
9.0	.728	-110.1	3.420	89.9	.104	23.9	.479	-69.1	0.55	10.7	15.2
10.0	.724	-117.8	3.304	83.8	.109	21.9	.468	-74.6	0.54	10.4	14.8
12.0	.722	-132.6	3.045	69.8	.115	14.7	.433	-86.7	0.56	9.7	14.2
14.0	.724	-146.6	2.876	57.2	.120	4.9	.398	-101.2	0.57	9.2	13.8
16.0	.714	-158.3	2.668	46.2	.125	-2.4	.376	-112.4	0.61	8.5	13.3
18.0	.695	-169.5	2.483	35.7	.132	-9.8	.373	-119.5	0.66	7.9	12.7
20.0	.676	-179.4	2.296	26.5	.143	-10.5	.394	-124.8	0.66	7.2	12.1
22.0	.665	168.5	2.115	13.7	.153	-14.9	.401	-130.3	0.68	6.5	11.4
24.0	.648	158.1	1.897	0.4	.163	-17.7	.388	-139.5	0.75	5.5	10.7
26.0	.632	147.8	1.817	-12.1	.167	-19.9	.378	-148.9	0.79	5.2	10.4
26.5	.641	145.0	1.832	-14.3	.168	-18.3	.372	-152.5	0.76	5.3	10.4

V_{DS} = 2 V, I_{DS} = 30 mA

FREQUENCY (GHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	S ₂₁ (dB)	MAG ² (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG			
0.1	.999	-2.0	7.441	178.7	.002	87.9	.484	-1.1	0.06	17.4	35.7
0.2	.999	-3.9	7.436	177.1	.003	86.5	.483	-2.7	0.04	17.4	33.9
0.5	.997	-9.5	7.422	173.1	.009	84.7	.483	-6.5	0.04	17.4	29.2
1.0	.991	-18.8	7.317	166.4	.017	82.2	.482	-12.8	0.04	17.3	26.3
2.0	.968	-36.6	7.041	153.1	.032	72.3	.472	-24.8	0.09	16.9	23.4
3.0	.929	-52.7	6.570	140.6	.047	63.9	.458	-36.3	0.16	16.3	21.4
4.0	.889	-66.4	6.058	129.9	.059	56.1	.447	-45.3	0.23	15.6	20.1
5.0	.846	-78.7	5.518	120.2	.067	50.5	.431	-52.3	0.31	14.8	19.1
6.0	.805	-89.3	5.083	111.5	.076	44.2	.411	-60.0	0.38	14.1	18.2
7.0	.777	-98.8	4.686	103.6	.083	39.5	.403	-64.1	0.44	13.4	17.5
8.0	.728	-107.8	4.335	96.3	.082	32.5	.375	-67.7	0.59	12.7	17.2
9.0	.709	-115.5	4.046	88.8	.084	30.6	.365	-70.9	0.65	12.1	16.8
10.0	.708	-123.2	3.879	82.9	.089	30.2	.359	-76.6	0.63	11.8	16.4
12.0	.707	-137.7	3.551	69.6	.097	23.8	.333	-89.5	0.64	11.0	15.6
14.0	.710	-151.1	3.293	57.0	.102	15.7	.311	-105.0	0.65	10.4	15.1
16.0	.704	-162.7	3.055	46.0	.110	8.8	.294	-117.1	0.67	9.7	14.4
18.0	.680	-173.2	2.835	35.9	.118	2.4	.300	-124.4	0.71	9.1	13.8
20.0	.667	177.0	2.598	27.1	.134	-0.5	.320	-128.7	0.69	8.3	12.9
22.0	.661	164.9	2.384	15.4	.149	-4.0	.336	-133.8	0.67	7.5	12.0
24.0	.654	153.8	2.141	3.1	.162	-6.8	.327	-141.0	0.70	6.6	11.2
26.0	.639	144.0	2.020	-9.2	.171	-10.4	.310	-150.5	0.75	6.1	10.7
26.5	.641	142.2	2.059	-11.6	.175	-11.7	.308	-156.2	0.72	6.3	10.7

See notes on back page.

TYPICAL COMMON SOURCE, REVERSE CHANNEL SCATTERING PARAMETERS¹ (T_A = 25°C)



V_{DS} = -2 V, I_{DS} = 10 mA

FREQUENCY (GHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	S ₂₁		MAG ² (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		(dB)	(dB)	
0.1	0.998	-0.8	1.492	-0.5	.003	93.9	.586	179.5	0.25	3.5	27.0	
0.2	0.999	-1.6	1.490	-1.3	.005	86.2	.587	179.3	0.12	3.5	24.7	
0.5	0.998	-3.8	1.489	-3.1	.013	89.7	.585	177.7	0.05	3.4	20.6	
1.0	1.000	-7.7	1.480	-5.9	.024	88.7	.588	175.6	-0.03	3.4	17.9	
2.0	0.998	-15.3	1.480	-11.9	.051	80.6	.585	171.0	0.02	3.4	14.6	
3.0	0.997	-22.	1.474	-17.9	.075	78.3	.582	167.0	0.01	3.4	12.9	
4.0	0.992	-29.5	1.464	-23.8	.101	73.5	.577	162.7	0.04	3.3	11.6	
5.0	0.987	-36.3	1.439	-29.2	.127	69.2	.573	158.5	0.06	3.2	10.5	
6.0	0.979	-42.9	1.428	-34.7	.151	64.8	.575	154.5	0.09	3.1	9.7	
7.0	0.965	-48.9	1.390	-40.2	.172	59.2	.573	151.1	0.15	2.9	9.1	
8.0	0.960	-55.1	1.379	-46.4	.191	55.5	.573	147.3	0.17	2.8	8.6	
9.0	0.955	-60.7	1.320	-52.2	.212	51.8	.574	143.4	0.18	2.4	7.9	
10.0	0.954	-66.6	1.323	-56.2	.243	47.2	.577	137.8	0.16	2.4	7.4	
12.0	0.968	-77.1	1.298	-66.4	.295	36.7	.578	125.1	0.13	2.3	6.4	
14.0	0.982	-87.3	1.301	-75.6	.348	24.6	.571	111.9	0.11	2.3	5.7	
16.0	0.986	-98.1	1.302	-85.8	.395	12.1	.530	99.8	0.14	2.3	5.2	
18.0	0.970	-108.8	1.268	-95.9	.453	1.1	.493	90.0	0.21	2.1	4.5	
20.0	0.962	-120.3	1.199	-104.0	.484	-7.5	.465	80.7	0.20	1.6	3.9	
22.0	0.978	-130.6	1.119	-113.2	.518	-16.8	.467	67.9	0.14	1.0	3.0	
24.0	1.039	-141.1	1.071	-123.5	.545	-23.7	.497	55.5	-0.00	0.6	2.9	
26.0	1.109	-152.1	1.076	-137.0	.574	-33.5	.485	40.8	-0.11	0.6	2.7	
26.5	1.112	-154.7	1.068	-140.6	.569	-36.8	.477	37.3	-0.11	0.6	2.7	

V_{DS} = -2 V, I_{DS} = 30 mA

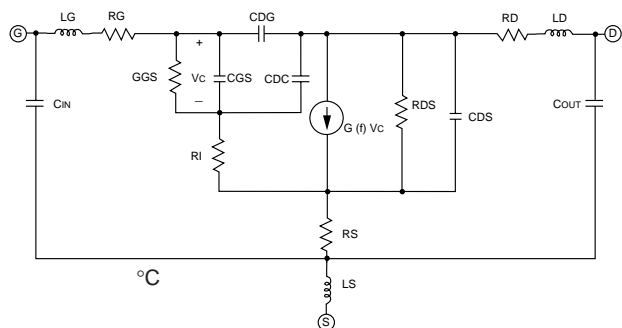
FREQUENCY (GHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂		K	S ₂₁		MAG ² (dB)
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		(dB)	(dB)	
0.1	0.999	-0.7	1.574	-0.3	.002	135.9	.687	179.7	-0.33	3.9	29.0	
0.2	1.000	-1.5	1.575	-1.3	.005	96.9	.686	179.2	-0.09	3.9	25.0	
0.5	0.998	-3.6	1.569	-2.9	.012	87.2	.687	177.8	0.06	3.9	21.2	
1.0	0.997	-7.4	1.565	-6.1	.022	87.9	.685	175.9	0.02	3.9	18.5	
2.0	0.998	-14.7	1.562	-12.0	.043	82.0	.684	171.3	0.01	3.9	15.6	
3.0	0.998	-21.6	1.558	-17.8	.066	79.8	.685	167.5	-0.01	3.8	13.7	
4.0	0.993	-28.3	1.550	-23.6	.087	75.1	.680	164.0	0.03	3.8	12.5	
5.0	0.990	-34.8	1.525	-28.9	.110	71.7	.678	159.7	0.02	3.7	11.4	
6.0	0.982	-41.3	1.518	-34.4	.132	67.0	.680	156.3	0.06	3.6	10.6	
7.0	0.966	-48.0	1.472	-39.7	.155	61.7	.677	153.1	0.11	3.4	9.8	
8.0	0.964	-54.4	1.463	-46.0	.172	57.8	.680	149.6	0.13	3.3	9.3	
9.0	0.961	-59.9	1.395	-52.0	.193	55.0	.684	145.7	0.13	2.9	8.6	
10.0	0.961	-65.9	1.401	-56.2	.220	51.0	.690	140.6	0.10	2.9	8.0	
12.0	0.974	-76.3	1.376	-65.7	.268	40.8	.700	128.7	0.07	2.8	7.1	
14.0	0.990	-86.5	1.378	-75.6	.319	28.9	.696	116.0	0.07	2.8	6.3	
16.0	0.998	-97.1	1.383	-85.8	.364	17.1	.651	104.3	0.10	2.8	5.8	
18.0	0.985	-107.9	1.350	-96.1	.417	6.0	.612	95.2	0.17	2.6	5.1	
20.0	0.982	-119.1	1.273	-104.0	.448	-2.0	.582	87.1	0.15	2.1	4.5	
22.0	0.995	-129.7	1.173	-112.5	.485	-11.7	.582	74.2	0.08	1.4	3.8	
24.0	1.056	-140.0	1.121	-122.6	.513	-18.5	.611	61.8	-0.07	1.0	3.4	
26.0	1.132	-150.8	1.118	-135.6	.537	-27.8	.606	48.3	-0.18	1.0	3.2	
26.5	1.123	-153.5	1.119	-139.9	.539	-30.6	.584	45.2	-0.15	1.0	3.2	

See notes on back page.

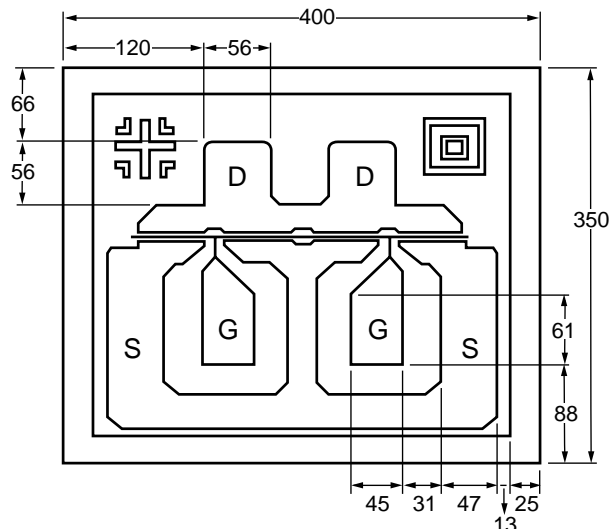
NE23300 LINEAR MODEL

CHIP DIMENSIONS (TA = 25°C)

SCHEMATIC 0.1- 26 GHz



NE23300 (CHIP)



Chip Thickness: 140 μm typical

Element Name	V _{DS} = 2 V, 0.1 < f < 26 GHz Element Value		Units
Cin		0.098	pF
Lg		19.544	nH
Ls		8.309	nH
Ld		12.998	nH
Cout		0.001	pF
CDS		0.028	pF
CDG		0.043	pF
CGS		0.000	S
CDC		0.084	pF
f		427.446	GHz
T		3.226	ps
	10 mA	20 mA	
RI	0.376	0.506	Ohms
RS	1.138	0.911	Ohms
RDS	209	162	Ohms
CGS	0.222	0.235	pF
G(f, Vc)	0.078	0.100	S

Notes:

1. S-Parameters include Bond Wires:

- Gate: Total 2 wires, 1 per bond pad 0.0129" (327 μm) long, each wire.
- Drain: Total 2 wires, 1 per bond pad 0.0118" (300 μm) long, each wire.
- Source: Total 4 wires, 2 per side, 0.0071" (180 μm) each wire.
- Wire: 0.0007" (17.8 μm) dia. gold.

2. Gain Calculations:

$$MAG = \frac{|S_{21}|}{|S_{12}|} (K \pm \sqrt{K^2 - 1}). \text{ When } K \leq 1, \text{ MAG is undefined and MSG values are used. } MSG = \frac{|S_{21}|}{|S_{12}|}, K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12} S_{21}|}, \Delta = S_{11} S_{22} - S_{21} S_{12}$$

MAG = Maximum Available gain
MSG = Maximum Stable Gain

EXCLUSIVE NORTH AMERICAN AGENT FOR **NEC** RF, MICROWAVE & OPTOELECTRONIC SEMICONDUCTORS

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